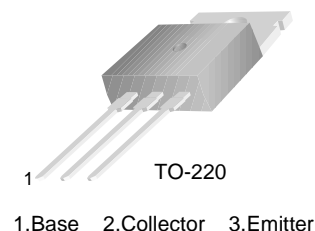


**■ ■ APPLICATION: AMPLIFIER APPLICATION,
 SWITCHING APPLICATION.**

■ ■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-80	V
Collector-emitter voltage	V_{CEO}	-80	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-6	A
Base current	I_B	-3	A
Collector Power Dissipation (Ta=25°C)	P_C	2	W
Collector Power Dissipation (Tc=25°C)	P_C	65	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-65~150	°C



■ ■ ELECTRICAL CHARACTERISTICSX

(Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE1}	15		75		$V_{CE} = -4V, I_C = -3A$
	h_{FE2}	30				$V_{CE} = -4V, I_C = -0.3A$
Collector-Emitter Cut-off Current	I_{CEO}			-0.7	mA	$V_{CE} = -60V, I_E = 0$
Emitter-Base Cut-off Current	I_{EBO}			-1	mA	$V_{EB} = -5V, I_C = 0$
Collector-Base Breakdown Voltage	BV_{CBO}	-80			V	$I_C = -1mA, I_E = 0$
Base-Emitter on Voltage	BV_{CEO}	-80			V	$I_C = -30mA, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	$I_E = -1mA, I_C = 0$
Base-Emitter on Voltage	V_{BE}			-2	V	$V_{CE} = -4V, I_C = -6A$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-1.5	V	$I_C = -6A, I_B = -0.6A$
Gain bandwidth product	f_T	3			MHz	$V_{CE} = -10V, I_C = -0.5A, f = 1MHz$

■ ■ hFE Classification And Marking

Print Mark

Classification

h_{FE}

15~75